Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claim 3 and accept amended claims 1, 4, 23, 25 and 26 as follows:

1. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode, comprising a first upper electrode and a second upper electrode, formed on the dielectric film, wherein:

the second upper electrode is formed by chemical vapor deposition and the first upper electrode is formed by physical vapor deposition,

a bias power is applied only to a target when the first upper electrode is formed by the physical vapor deposition, and

the capacitor is a concave-type capacitor.

2. (original) The capacitor of claim 1, wherein the upper electrode is made of one selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, ruthenium, platinum, iridium, and a combination thereof.

3. (canceled)

4. (currently amended) The capacitor of claim 1, wherein ~~the upper electrode includes a first upper electrode formed by the physical vapor deposition and a second~~

~~upper electrode formed by the chemical vapor deposition and~~ the first upper electrode and the second upper electrode are sequentially stacked.

5. - 22. (canceled)

23. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

~~the upper electrode is formed by physical vapor deposition and one of chemical vapor deposition and atomic layer deposition,~~

the upper electrode includes a first upper electrode formed by physical vapor deposition and a second upper electrode formed by one of chemical vapor deposition and atomic layer deposition,

a bias power is applied only to a target when the first upper electrode is formed by the physical vapor deposition, and

the capacitor is a concave-type capacitor.

24. (canceled)

25. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

~~the upper electrode is formed by chemical vapor deposition and physical vapor deposition, and~~

the upper electrode includes a first upper electrode formed by physical vapor deposition and a second upper electrode formed by chemical vapor deposition, and

a bias power is applied only to a target when the first upper electrode is formed by the physical vapor deposition~~; and~~

~~an anti-reflective layer formed on the second upper electrode~~.

26. (currently amended) The capacitor of claim 25, ~~wherein the capacitor is a concave-type capacitor~~ further comprising an anti-reflective layer formed on the second upper electrode.